

## Section 19 Introduction to PN Junctions

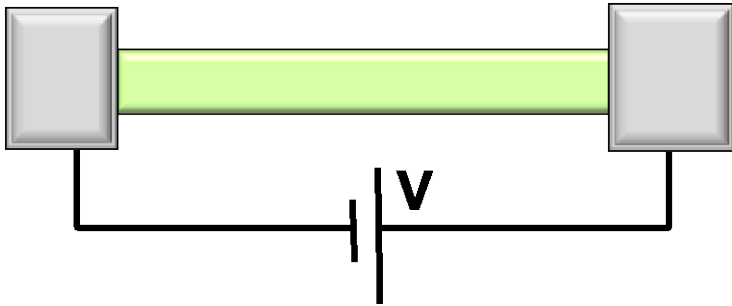
Gerhard Klimeck

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School of Electrical and  
Computer Engineering

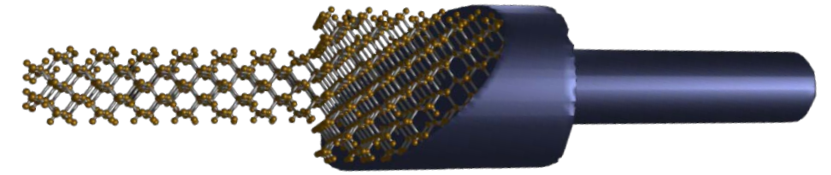
# Current Flow Through Semiconductors



$$I = G \times V$$

$$= q \times n \times v \times A$$

↑ charge density    ↑ density    ↑ velocity    ↑ area



- **Materials, composition, crystals**
- Tabulated for **“known” bulk materials**
- At nm-scale properties change with geometry => theory  
=> Quantum Mechanics
- Concepts of **density of states and masses**  
=> Equilibrium Statistical Mechanics
- **Occupation factors**

Transport with scattering, non-equil. Stat. Mech.

- **Drift-diffusion Eq. with recombination-generation**

**Understanding transport in concrete devices**

PN Diode    Schottky Diode

BJT/ HBT    MOS

$$\nabla \cdot D = q(p - n + N_D^+ - N_A^-)$$

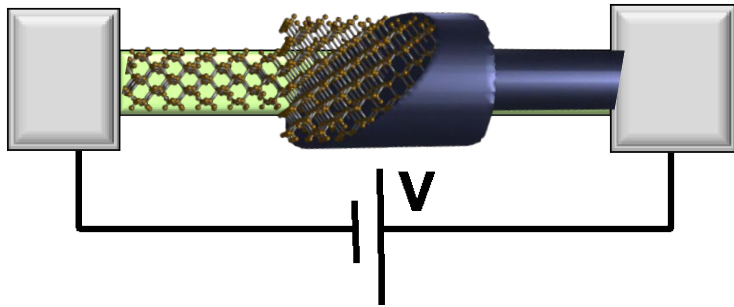
$$\frac{\partial n}{\partial t} = \frac{1}{q} \nabla \cdot \mathbf{J}_N - r_N + g_N$$

$$\mathbf{J}_N = qn\mu_N E + qD_N \nabla n$$

$$\frac{\partial p}{\partial t} = \frac{-1}{q} \nabla \cdot \mathbf{J}_P - r_P + g_P$$

$$\mathbf{J}_P = qp\mu_P E - qD_P \nabla p$$

# Topic Map



$$I = G \times V$$

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↑ charge density    ↑ velocity    area

	Equilibrium				
PN Diode					
Schottky Diode					
BJT/ HBT					
MOS					

$$\nabla \cdot D = q(p - n + N_D^+ - N_A^-)$$

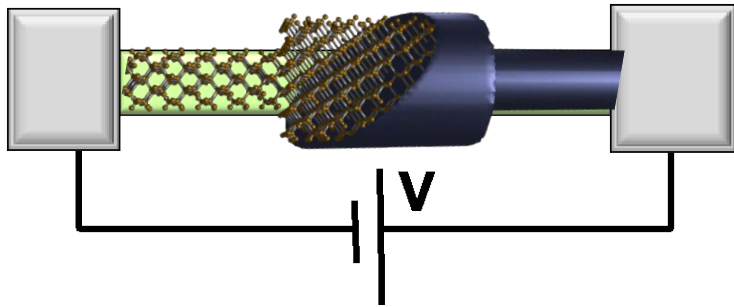
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	Equilibrium	DC			
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Schottky Diode					
BJT/ HBT					
MOS					

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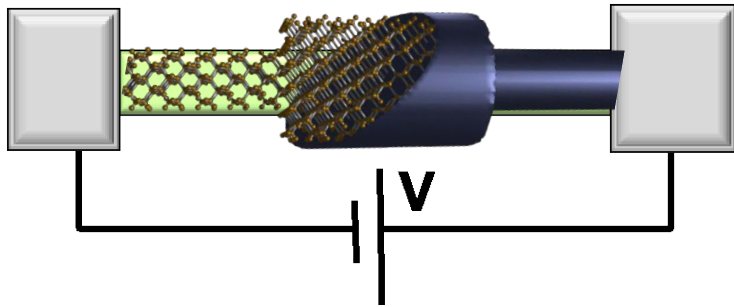
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$$I = G \times V$$

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↑ charge density    ↑ velocity    area

	Equilibrium	DC	Small signal	Large Signal	Circuits
PN Diode					
Schottky Diode					
BJT/ HBT					
MOS					

$$\nabla \cdot D = q(p - n + N_D^+ - N_A^-)$$

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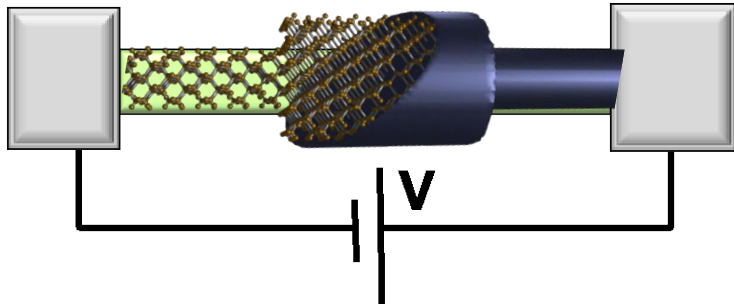
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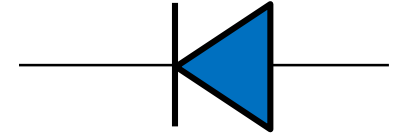
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$$I = G \times V$$

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↑ charge density    ↑ velocity    ↑ area



	Equilibrium	DC	Small signal	Large Signal	Circuits
PN Diode					
Schottky Diode		Diode in Equilibrium. (No external voltage applied)			
BJT/ HBT					
MOS					

$$\nabla \cdot D = q(p - n + N_D^+ - N_A^-)$$

$$\frac{\partial n}{\partial t} = \frac{1}{q} \nabla \cdot \mathbf{J}_N - r_N + g_N$$

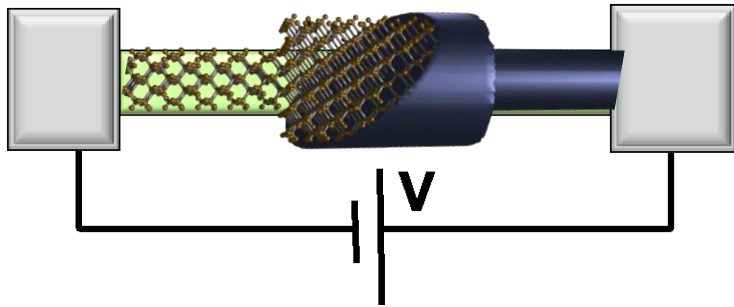
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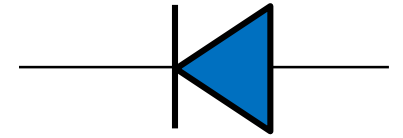
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Vid

- 19.1 Structure and Depletion Region

Vid

- 19.2 Drawing band-diagrams in equilibrium



$$\nabla \cdot D = q(p - n + N_D^+ - N_A^-)$$

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# What is a Diode good for ....

solar cells



GaAs lasers



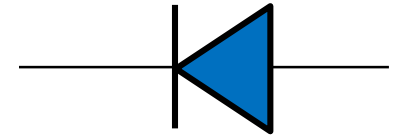
Organic LED



Avalanche Photodiode



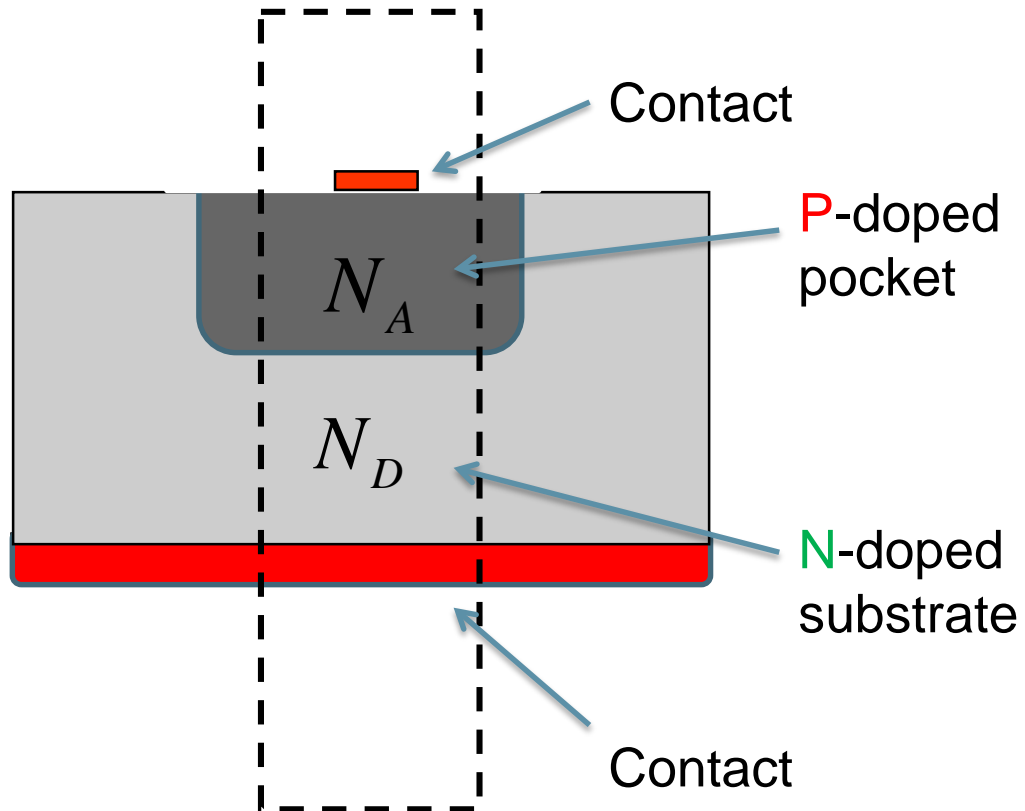
GaN lasers



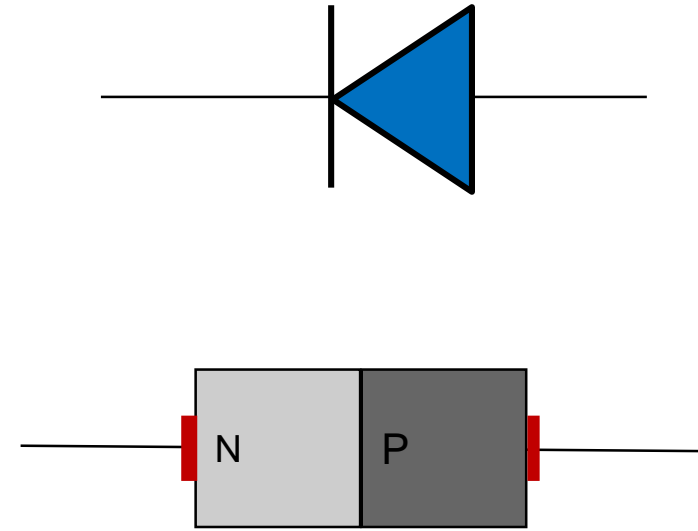


# p-n Junction Devices ...

## Schematic of a p-n Diode



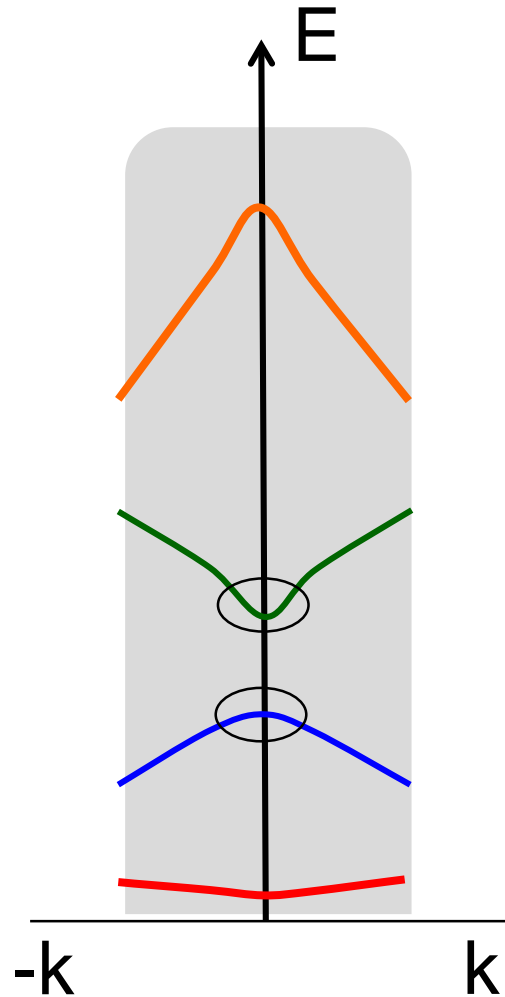
## Symbol



Point-contact diode

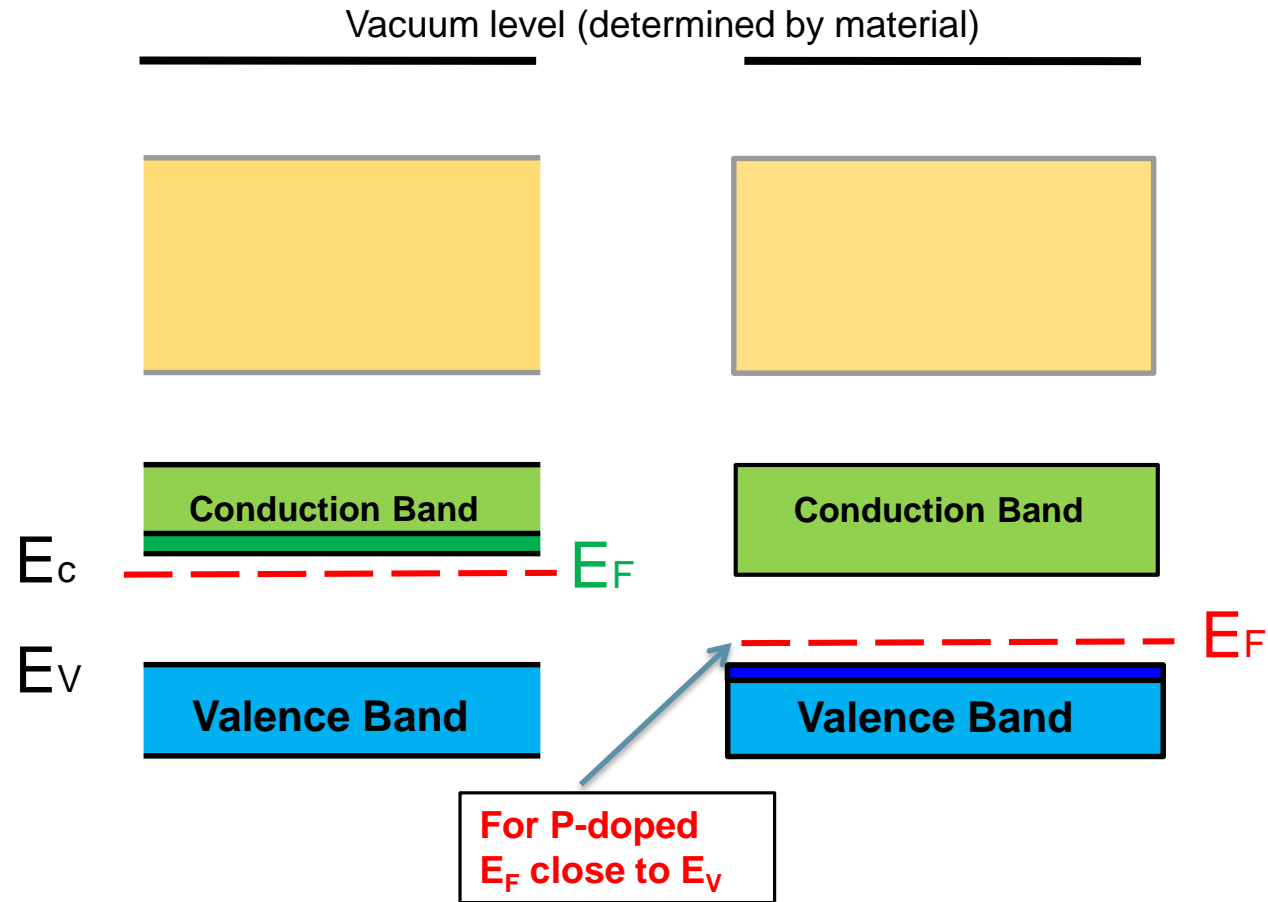


# P and N doped Material Side by Side ...

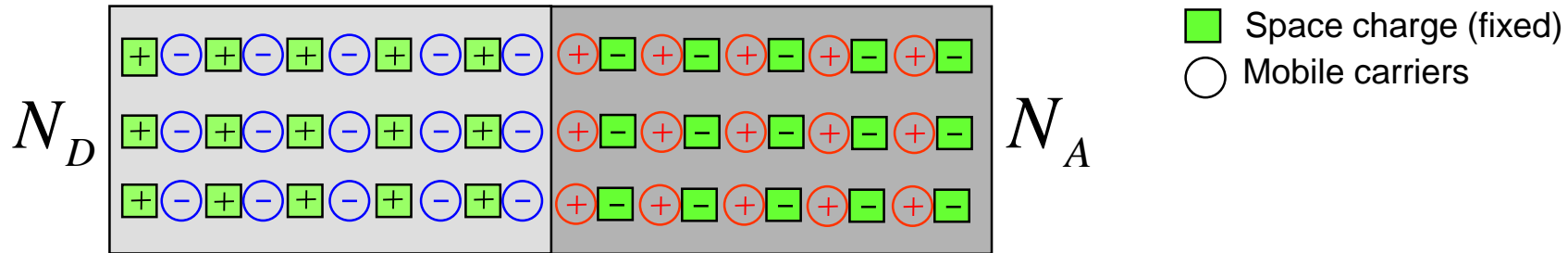


N-doped

P-doped



# Forming a Junction



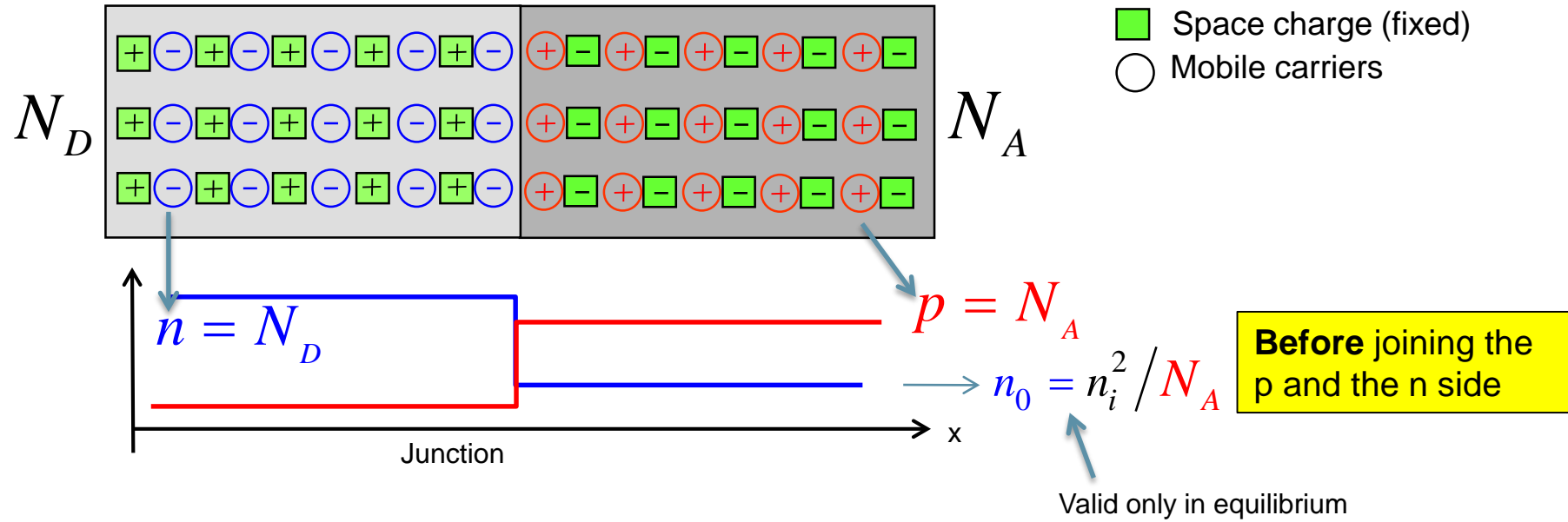
## Donor-side (N-side)

**Squares** are fixed **donor atoms**.  
Every donor atom has given away one **electron** (blue **circle**)

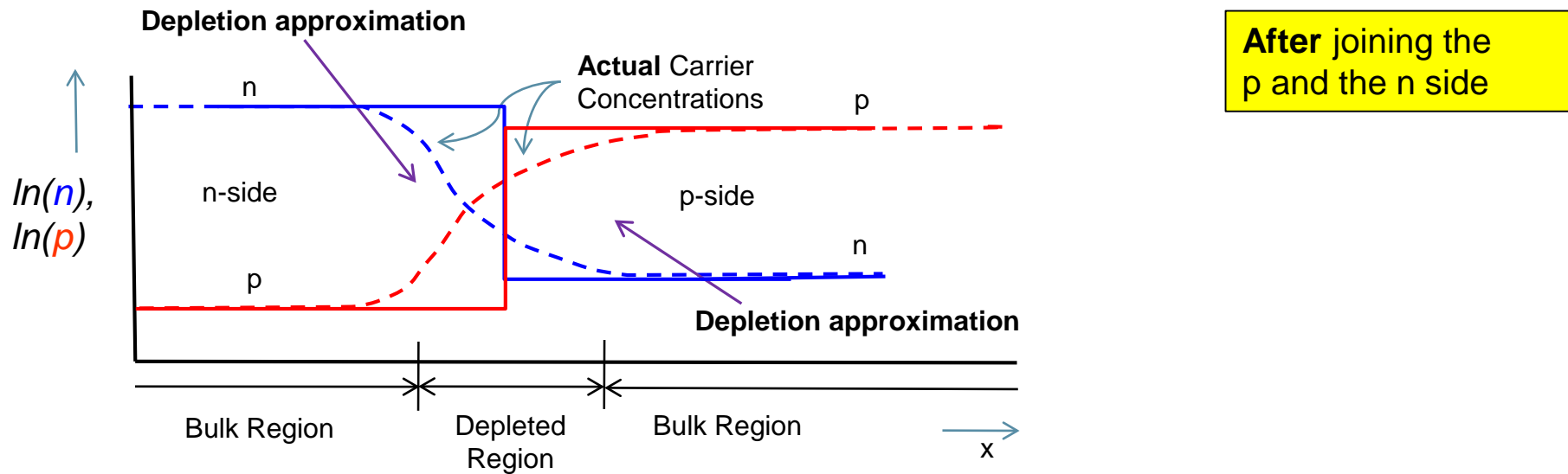
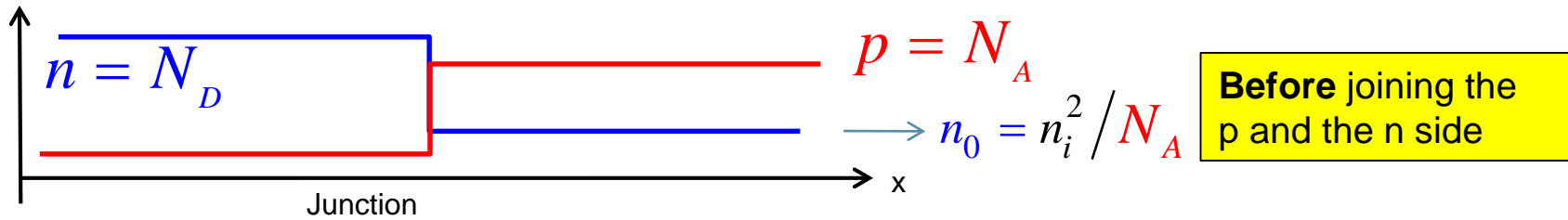
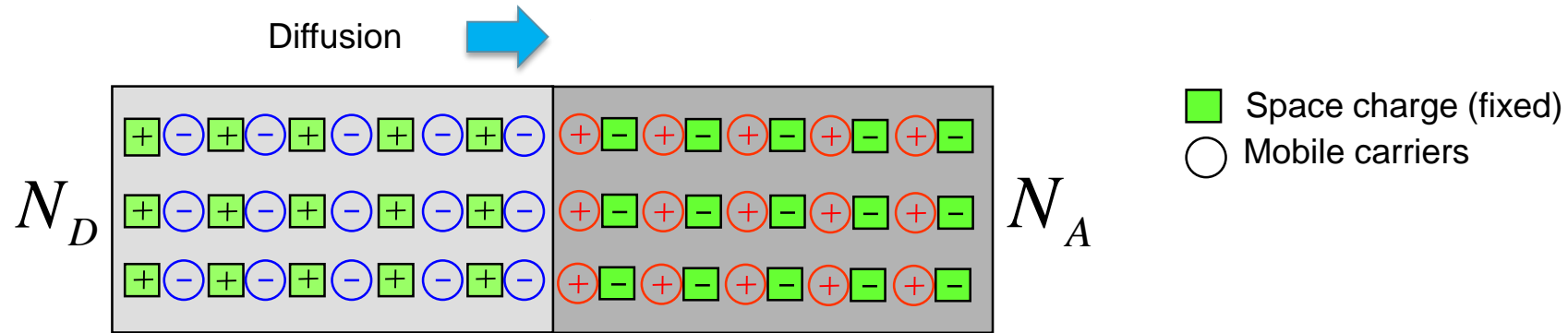
## Acceptor-side (P-side)

**Squares** are fixed **acceptor atoms**.  
Every acceptor atom has captured one **electron** (from the valence band).  
Every acceptor atom leaves behind one **hole** in the valence band. (red **circle**)

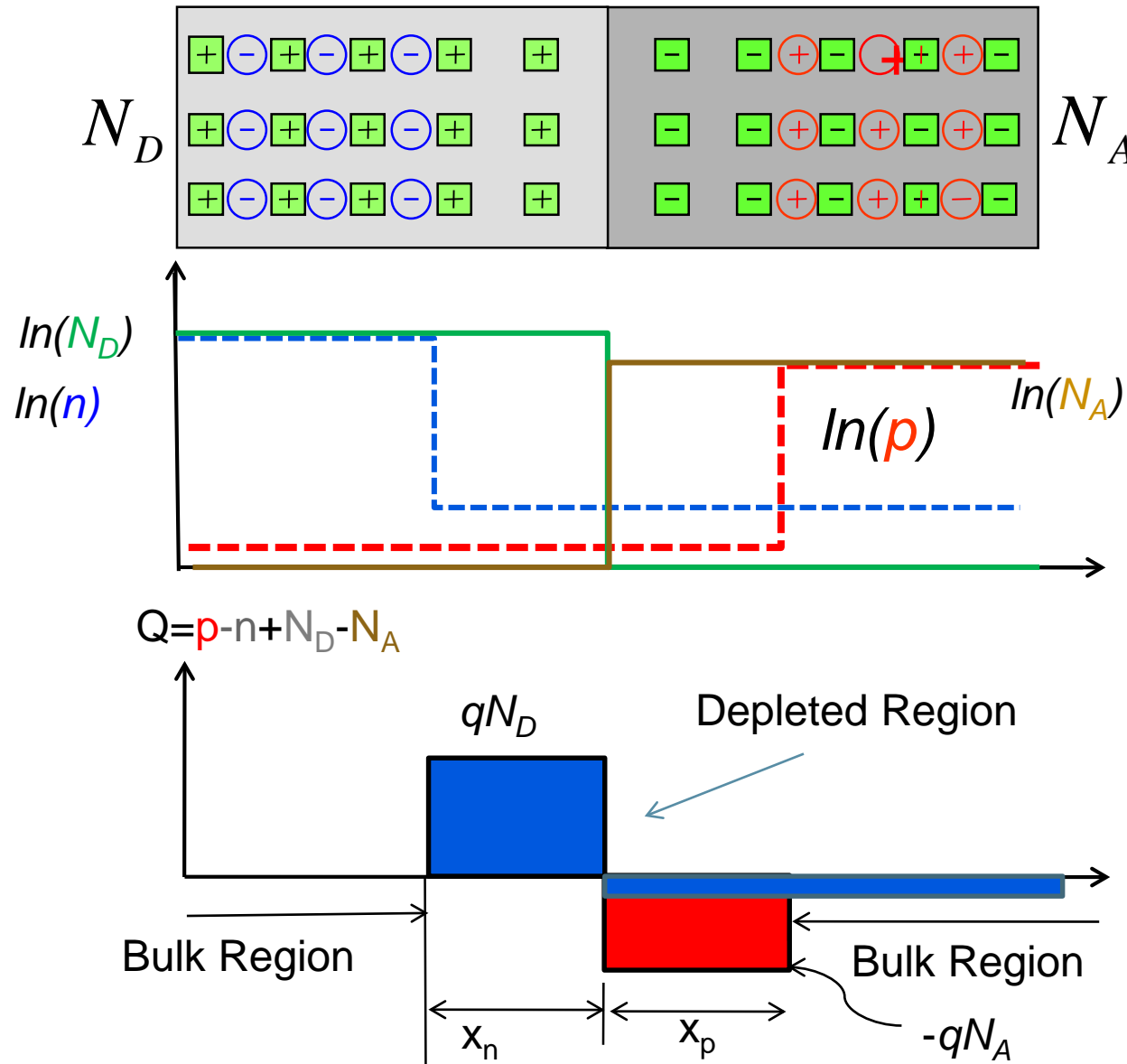
# Forming a Junction



# Forming a Junction



# Formation of a Junction



Net charge on **N-side**:  $qN_D$   
 (subtract green from blue line)  
 Space charge region: fixed donor atoms  
 Neglect electrons in p-side  
 $X_n$ : depletion region in N-side

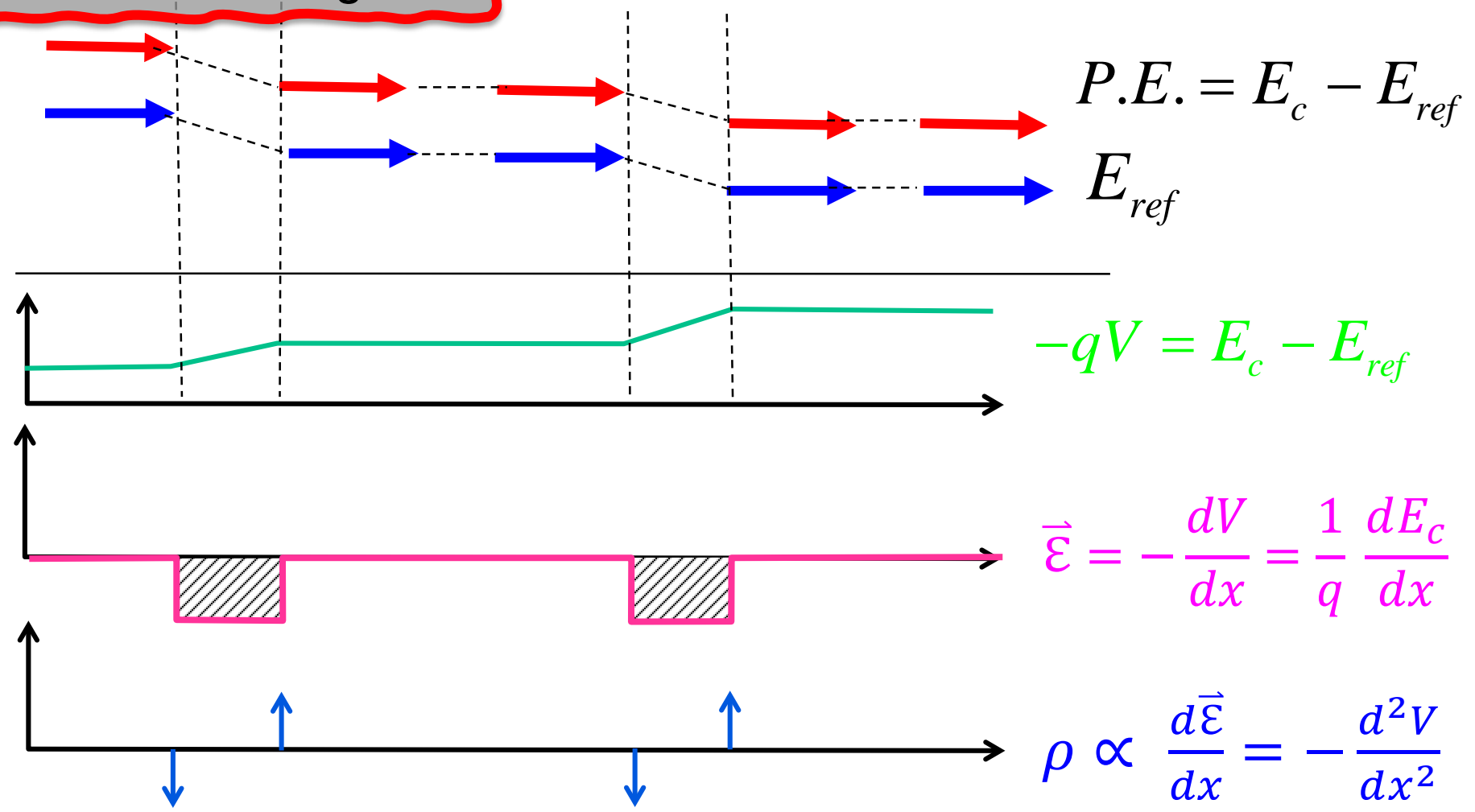
Net charge on **P-side**:  $-qN_A$   
 (subtract brown from red line)  
 Space charge region: fixed acceptor atoms  
 $X_p$ : depletion region in P-side

red and blue are of equal size  
 $\rightarrow$  **charge balance**

**Depletion Region** means  
 depleted of "mobile" charges

# Potential, Field and Charge

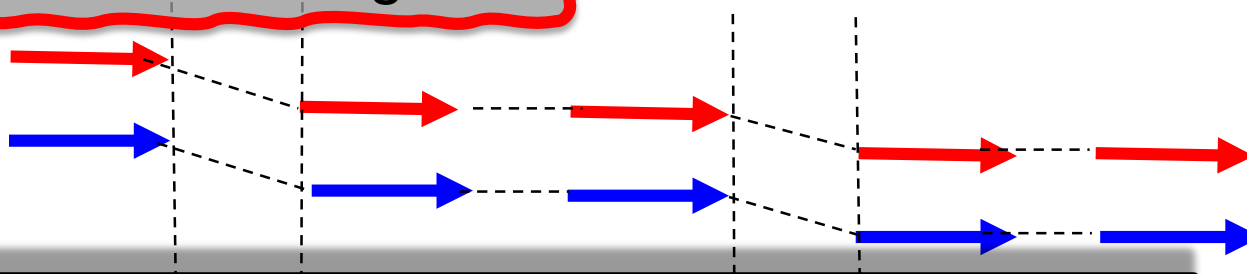
From Section 13 – Band Diagrams



In most practical cases start from charge and derive potentials!  
=> Useful to learn “graphical” integration

# Potential, Field and Charge

From Section 13 – Band Diagrams



$$P.E. = E_c - E_{ref}$$

$$E_{ref}$$



$$-qV = E_c - E_{ref}$$

$$\vec{\epsilon} = -\frac{dV}{dx} = \frac{1}{q} \frac{dE_c}{dx}$$

$$\rho \propto \frac{d\vec{\epsilon}}{dx} = -\frac{d^2V}{dx^2}$$

**Sketch of Electrostatics**

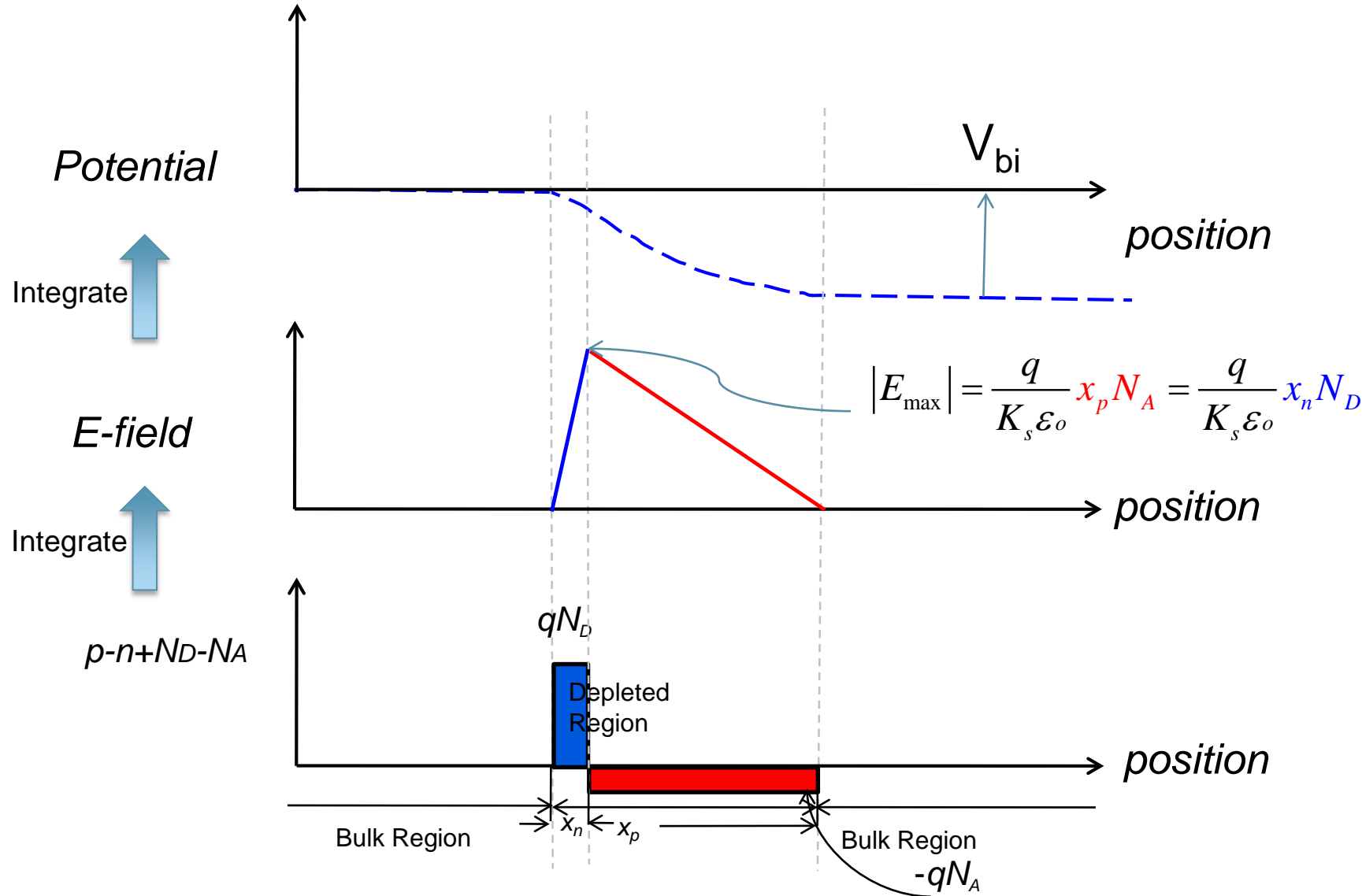
Klimeck – Solid State Devices  
13

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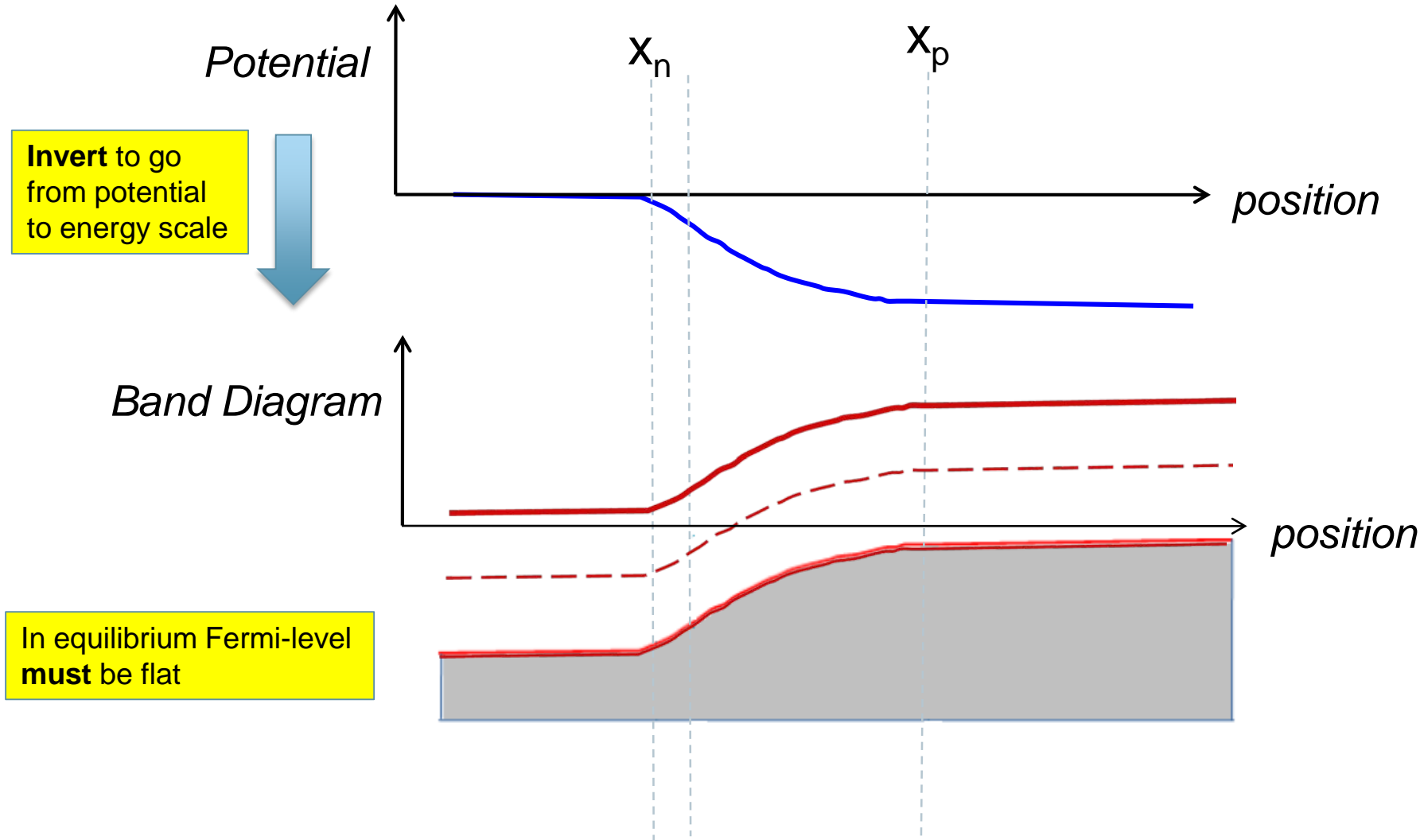


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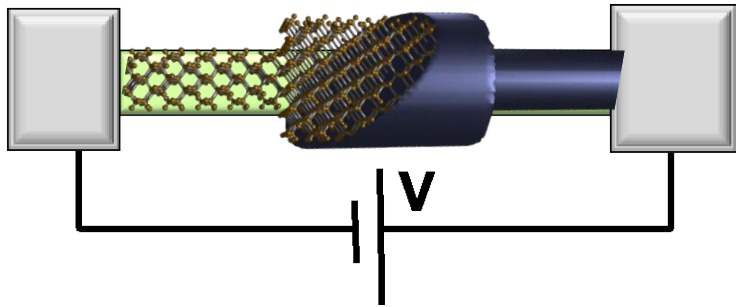
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# Sketch of Electrostatics



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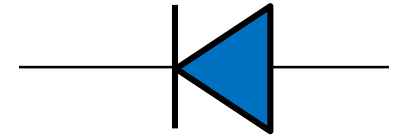
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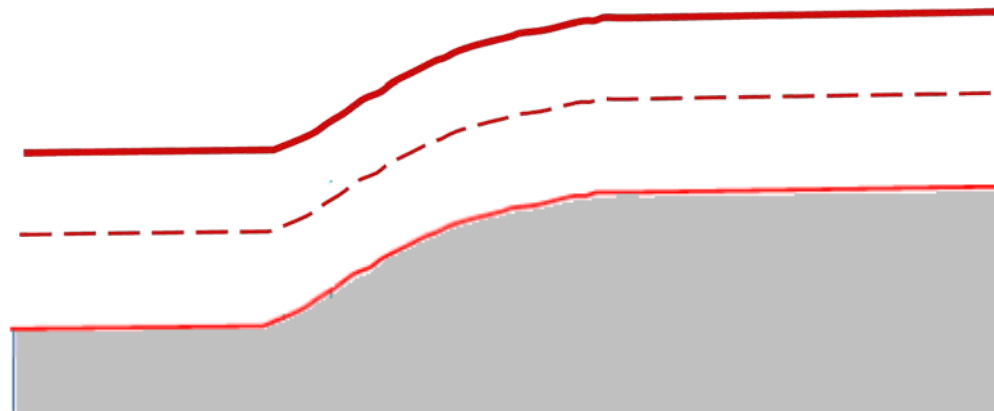
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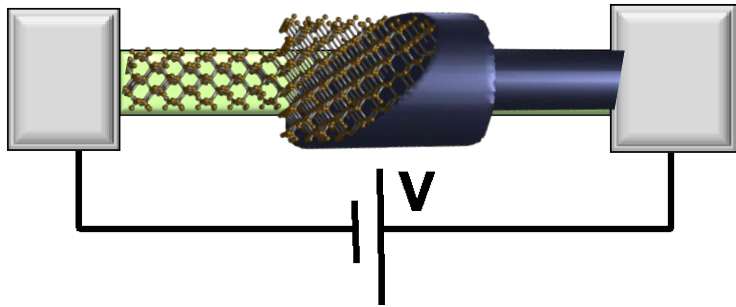
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Vi

Vid

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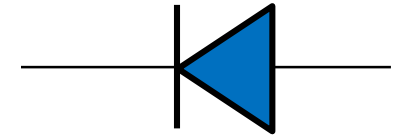
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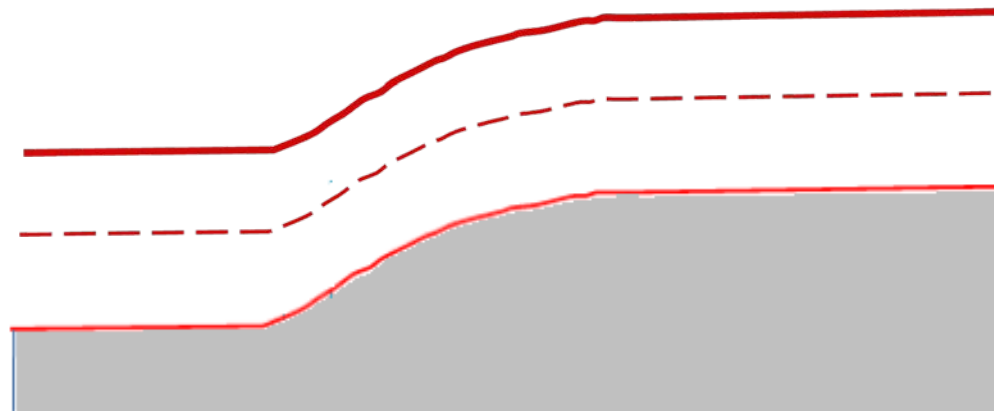
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